

BSS100L / BSS123

FEATURES

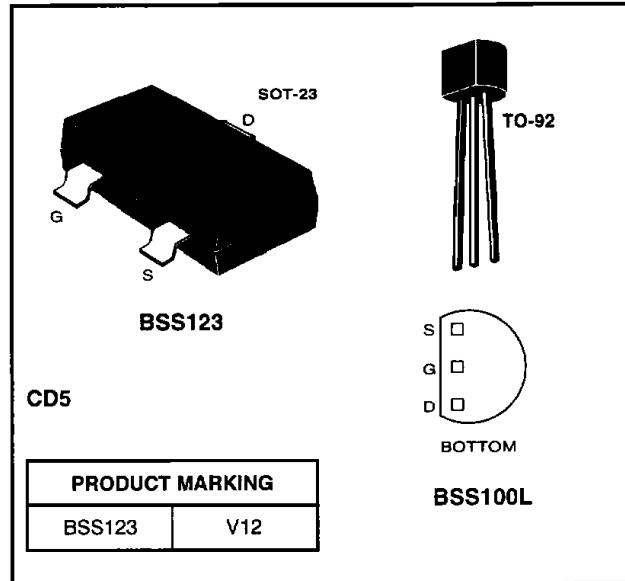
- Compact Geometry
- Fast Switching Speeds
- No Secondary Breakdown
- Excellent Temperature Stability
- High Input Impedance
- Low Current Drive
- Ease of Paralleling

APPLICATIONS

- Small Motor Drivers
- Switches
- Amplifiers

ORDERING INFORMATION

Part	Package	Temperature Range
BSS123	Surface Mount SOT-23	-55°C to +150°C
BSS100L	Plastic TO-92	-55°C to +150°C
XBSS123	Sorted Chips in Carriers	-55°C to +150°C



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETERS	BSS100L	BSS123	UNITS
V _{DS}	Drain-Source Voltage	100	100	V
I _D	Continuous Drain Current (@ T _A = 25°C)	170	170	mA
I _{DM}	Pulsed Drain Current	680	680	mA
V _{GS}	Gate-Source Voltage	±20	±20	V
P _D	Max. Power Dissipation (@ T _A = 25°C)	.2	0.36	W
T _J , T _{stg}	Operating/Storage Temperature Range	-50 to +150	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
BV_{DSS}	Drain-Source Breakdown Voltage	100			V	$I_D = 0.25\text{mA}, V_{GS} = 0\text{V}$
$V_{GS(\text{th})}$	Gate-Source Threshold Voltage	0.8	2.2	2.8	V	$I_D = 1\text{mA}, V_{DS} = V_{GS}$
I_{GSS}	Gate-Body Leakage		10	50	nA	$V_{GS} = 20\text{V}, V_{DS} = 0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current		1 2	15 50 10	μA μA nA	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}, T = 25^{\circ}\text{C}$ $V_{DS} = 100\text{V}, V_{GS} = 0\text{V}, T = 125^{\circ}\text{C}^2$ $V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T = 25^{\circ}\text{C}$
$R_{DS(\text{ON})}$	Static Drain-Source On-State Resistance ¹		5	6	Ω	$I_D = 100\text{mA}, V_{GS} = 10\text{V}$
g_{fs}	Forward Transconductance ^{1,2}	80	120		mS	$V_{DS} = 25\text{V}, I_D = 100\text{mA}$
C_{iss}	Input Capacitance ²		20		pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
C_{oss}	Common Source Output Capacitance ²		9			
C_{rss}	Reverse Transfer Capacitance ²		4			
$t_{d(\text{ON})}$	Turn-On Delay Time ^{2,3}		10		ns	$V_{DD} = 30\text{V}, I_D = 280\text{mA}$
t_r	Rise Time ^{2,3}		10			
$t_{d(\text{OFF})}$	Turn-Off Delay Time ^{2,3}		15			
t_f	Fall Time ^{2,3}		25			

Notes:

1. Measured under pulsed conditions. Width = 300 μs . Duty cycle $\leq 2\%$.
2. Sample test.
3. Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator.